



#### 40V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>C</sub> = +25°C	
40V	4.7mΩ @ V <sub>GS</sub> = 10V	100A	

# **Description and Applications**

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

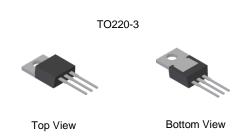
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

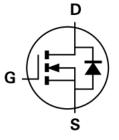
### **Features**

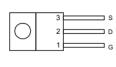
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: TO220-3
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)







Equivalent Circuit

Top View Pin Out Configuration

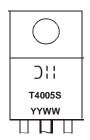
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMT4005SCT	TO220-3	50 pieces/tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Dil = Manufacturer's Marking
T4005S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	$V_{DSS}$	40	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Ocaliana Paris Ocaras (Alata O)	T <sub>C</sub> = +25°C	I <sub>D</sub>	100	А
Continuous Drain Current (Note 6)	T <sub>C</sub> = +70°C		85	
Maximum Continuous Body Diode Forward Current (Note 6)	T <sub>C</sub> = +25°C	Is	85	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	160	А	
Avalanche Current, L=0.1mH	I <sub>AS</sub>	32.5	Α	
Avalanche Energy, L=0.1mH	E <sub>AS</sub>	52.8	mJ	

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	52.8	°C/W
Total Power Dissipation (Note 6)	T <sub>C</sub> = +25°C	P <sub>D</sub>	104	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.2	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

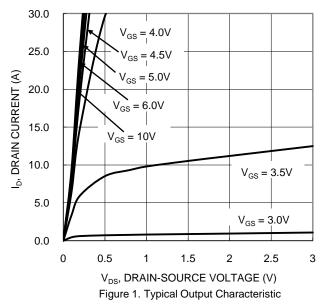
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

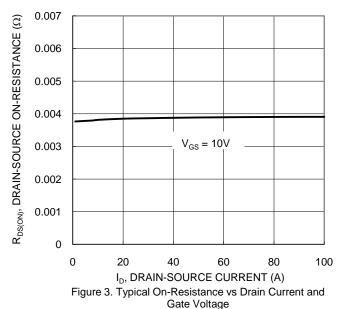
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)		,					
Gate Threshold Voltage	$V_{GS(TH)}$	2	_	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	1	3.8	4.7	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	$V_{SD}$		_	1.2	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	3062	_		V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	902	1	pF		
Reverse Transfer Capacitance	Crss	-	179	-			
Gate Resistance	$R_G$	_	0.67	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	49.1	_		$V_{DD} = 20V, I_D = 50A,$	
Gate-Source Charge	Qgs	_	10.3	_	nC		
Gate-Drain Charge	$Q_{gd}$	_	13	_		V <sub>GS</sub> = 10V	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.7	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{G} = 3\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	6.8	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	18.6	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	7.3	_			
Reverse Recovery Time	t <sub>RR</sub>	_	31.8	_	ns	I F0.0 di/dt _ 1000/up	
Reverse Recovery Charge	Q <sub>RR</sub>	_	26.5	_	nC	I <sub>F</sub> = 50A, di/dt = 100A/μs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on infinite heat sink. Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







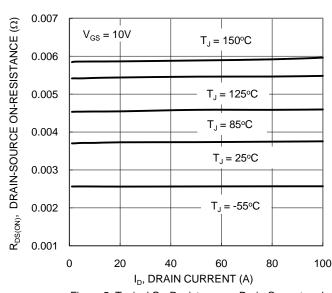


Figure 5. Typical On-Resistance vs Drain Current and Temperature

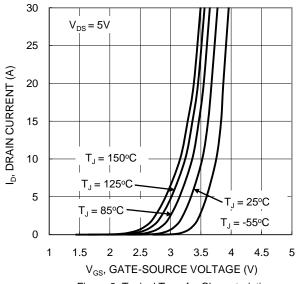


Figure 2. Typical Transfer Characteristic

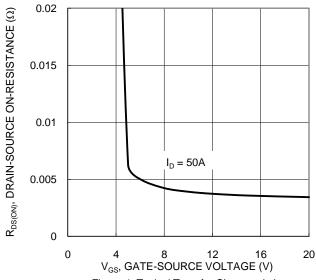


Figure 4. Typical Transfer Characteristic

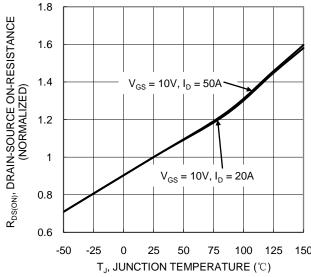


Figure 6. On-Resistance Variation with Temperature



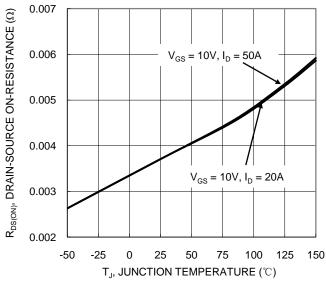
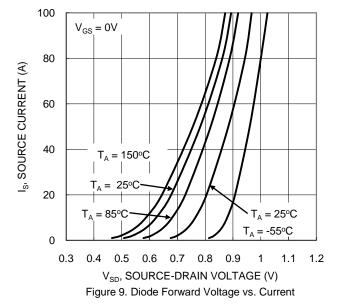
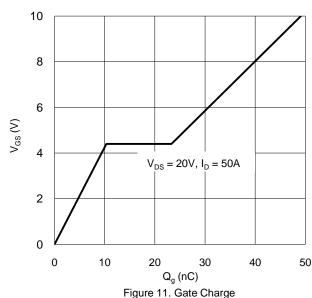


Figure 7. On-Resistance Variation with Temperature





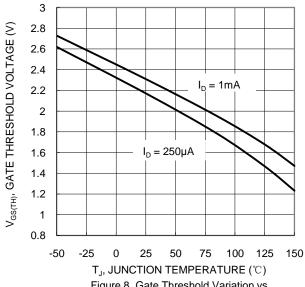


Figure 8. Gate Threshold Variation vs Temperature

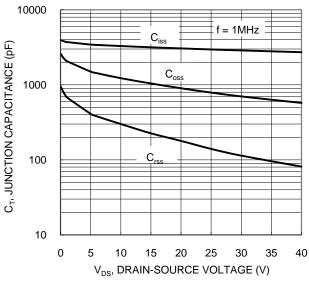
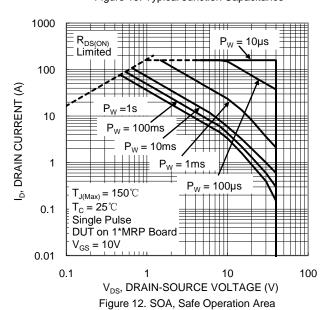


Figure 10. Typical Junction Capacitance





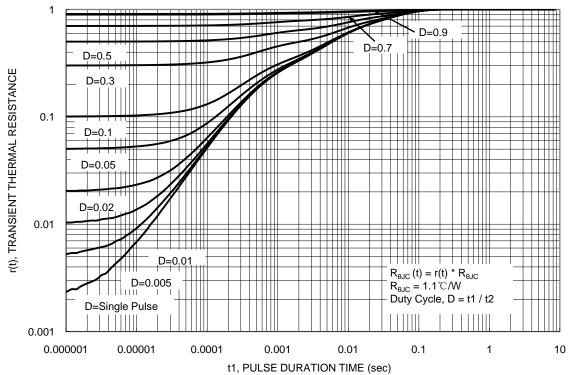
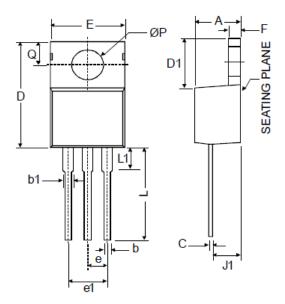


Figure 13. Transient Thermal Resistance

## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO220-3



TO220-3				
Dim	Min	Max		
Α	3.55	4.85		
b	0.51	1.14		
b1	1.14	1.78		
С	0.31	1.14		
D	14.20	16.50		
D1	5.84	6.86		
Е	9.70	10.70		
е	2.79	2.99		
e1	4.83	5.33		
F	0.51	1.40		
J1	2.03	2.92		
L	12.72	14.72		
L1	3.66	6.35		
Р	3.53	4.09		
Q	2.54	3.43		
All Dimensions in mm				



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